IN THE CLAIMS:

Claims 1 through 7 have been amended herein. All of the pending claims 1 through 7 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

- 1. (Currently amended) A method of forming a semiconductor device assembly, said method comprising:
- providing a substrate having an upper surface and a lower surface;
- depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;
- patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
- depositing at least one layer of metal on at least a portion of the layer of copper; and connecting one end of a-conductor-conductive lead of a TAB tape to the at least one layer of metal.
- (Currently amended) The method of claim 1, further comprising:
 connecting one end of the conductor conductive lead of the TAB tape to the at least one layer of metal using a wire bond.
- 3. (Currently amended) A method of forming a semiconductor device assembly, said method comprising:
 providing a substrate having an upper surface and a lower surface;
 depositing a layer of copper on the one surface of the upper surface and the lower surface of the substrate;

patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; and connecting one end of a-conductor-conductive lead of a TAB tape to the at least one layer of gold metal.

- 4. (Currently amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;
- patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of metal on at least a portion of the layer of copper; and connecting one end of a-conductor-conductive lead of a TAB tape to the at least one layer of metal.

- (Currently amended) The method of claim 4, further comprising:
 connecting one end of the conductor conductive lead of the TAB tape to the at least one layer of metal using a wire bond.
- 6. (Currently amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;

patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; and

connecting one end of a-conductor-conductive lead of a TAB tape to the at least one layer of gold metal.

- 7. (Currently amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;
- patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
- depositing at least one layer of gold metal on at least a portion of the layer of copper; and connecting one of an end of a conductor conductive lead of a TAB tape and a portion of a bond wire to the at least one layer of gold metal.